

SOT-89 Plastic-Encapsulated Transistors

2SB1132 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM}: 0.5 \text{ W (Tamb=25°C)}$$

Collector current

$$I_{CM}: -1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: -40 \text{ V}$$

Operating and storage junction temperature range

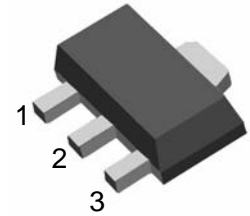
$$T_J, T_{stg}: -55°C \text{ to } +150°C$$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-50\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-20V, I_E=0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4V, I_C=0$			-0.5	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-3V, I_C=-100mA$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-50mA$			-0.5	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-50mA, f=30MHz$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		20	30	pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	P	Q	R
Range	82-180	120-270	180-390
Marking	BAP	BAQ	BAR